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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of : Confirmation No. 3756

Tomohiro OKUMURA et al. : Docket No. 2000-0191A

Serial No. 09/511,398 : Group Art Unit 1762

Filed February 23, 2000 : Examiner M. Padgett

PLASMA PROCESSING METHOD
AND APPARATUS :

THE COMMISSIONER IS AUTHORIZED
TO CHARGE ANY DEFICIENCY IN
FEES FOR THIS PAPER TO DEPOSIT
ACCOUNT NO. 23-0975

AMENDMENT

Assistant Commissioner for Patents,
Washington, D.C. 20231

Sir:

Responsive to the Office Action of September 20, 2003, a three month extension of time
being filed concurrently herewith, please amend the above-identified application as follows.

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In the Specification:

Page 21, please replace paragraph [0114] with the following rewritten paragraph:

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[0114] Fig. 1A shows a sectional view of a plasma processing apparatus employed in the first embodiment of the present invention. Referring to Fig. 1A, while the interior of a vacuum chamber 1 is maintained at a specified pressure by introducing a specified gas from a gas supply unit 2 into the vacuum chamber 1 and by simultaneously performing evacuation by a pump 3 as an evacuating device, a high-frequency power of 100 MHz is supplied to a counter electrode 5 by a counter-electrode-use-high-frequency power supply 4. Then, plasma is generated in the vacuum chamber 1, where plasma processing such as etching, deposition, and surface reforming can be carried out on a substrate 7 placed on a substrate electrode 6. A substrate-electrode-use-high-frequency